

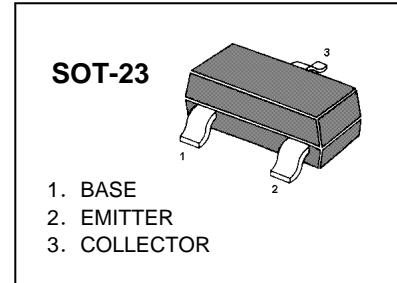
Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

FEATURES

LOW $V_{CE(sat)}$

Marking: DT



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	2	A
P_C	Collector Power Dissipation	0.3	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=0.5\text{A}$	120		270	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=1.5\text{A}$	45			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=50\text{mA}$			0.35	V
Transition frequency	f_T	$V_{CE}=2\text{V}, I_C=0.5\text{A}, f=100\text{MHz}$		210		MHz
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		21		pF



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Typical Characteristics

